

What is claimed is:

1. A display having a reflective region and a transmissive region comprising:

a projecting insulating layer formed in a region corresponding to said reflective region on a substrate; and
a light shielding layer formed under said projecting insulating layer and formed to extend at least up to a region in which a side end of said projecting insulating layer is located.

2. A display according to claim 1, wherein said projecting insulating layer is formed to surround said transmissive region, as viewed in a plan view; and

said light shielding layer is formed to extend up to said transmissive region beyond a region in which the side end of said projecting insulating layer is located.

3. A display according to claim 1, further comprising:

a thin film transistor formed between said projecting insulating layer and said substrate and having a pair of source/drain regions and a gate electrode;

wherein said light shielding layer is formed of the same layer as that constituting said gate electrode.

4. A display according to claim 1, further comprising:

a storage capacitance having a storage capacitance line;

wherein said light shielding layer is formed of the same layer as that constituting the storage capacitance line of said storage capacitance.

5. A display according to claim 1, further comprising:

a black matrix layer formed between said projecting insulating layer and said substrate;

wherein said light shielding layer is formed of the same layer as that constituting said black matrix layer.

6. A display according to claim 5, further comprising:

a thin film transistor formed between said projecting insulating layer and said substrate and having a pair of source/drain regions and a gate electrode, to which a gate line is connected;

wherein said light shielding layer formed of the same layer as that constituting said black matrix layer is formed to overlap with said gate line.

7. A display according to claim 1, wherein said projecting insulating layer has a finely uneven diffusion region at the upper surface thereof.

8. A display according to claim 1, wherein a side end of said projecting insulating layer has an inclined side surface; and

there is further provided a reflecting film formed not at the side surface of said projecting insulating layer but at the upper surface of said projecting insulating layer.

9. A display according to claim 1, wherein a side end of said projecting insulating layer has an inclined side surface; and

there is further provided a reflecting film formed at the upper surface and side surface of said insulating layer.

10. A display according to claim 1, further comprising:

a thin film transistor formed between said projecting insulating layer and said substrate and having a pair of source/drain regions and a gate electrode; and

a storage capacitance having a storage capacitance

line;

wherein said light shielding layer is formed of a layer constituting said gate electrode and a layer constituting said storage capacitance line.

11. A display according to claim 10, wherein the layer constituting said gate electrode and the layer constituting said storage capacitance line are formed of the same layer.

12. A display having a substrate, a projecting insulating layer on said substrate, a first electrode on said substrate, a second electrode on said first electrode and a liquid crystal layer held between said first electrode and said second electrode, the display comprising:

a transmissive region, in which said first electrode is made of transparent material, and said first electrode and said second electrode are separated from each other with a first distance;

a reflective region including a reflector on said projecting insulating layer, in which said first electrode and said second electrode are separated from each other with a second distance shorter than said first distance due to said projecting insulating layer; and

a light shielding layer interposed between said substrate and said projecting insulating layer,

said light shielding layer extending at least up to an end on the side of said transmissive region of said projecting insulating layer.

13. A display according to claim 12, wherein said projecting insulating layer is formed to surround said transmissive region, as viewed in a plan view; and

said light shielding layer is formed to extend up to said transmissive region beyond a region in which the side end of said projecting insulating layer is located.

14. A display according to claim 12, further comprising:

a thin film transistor formed between said projecting insulating layer and said substrate and having a pair of source/drain regions and a gate electrode,

wherein said light shielding layer is formed of the same layer as that constituting said gate electrode.

15. A display according to claim 12, further comprising:

a storage capacitance having a storage capacitance line,

wherein said light shielding layer is formed of the same layer as that constituting the storage capacitance line of said storage capacitance.

16. A display according to claim 12, further comprising:

a black matrix layer formed between said projecting insulating layer and said substrate,

wherein said light shielding layer is formed of the same layer as that constituting said black matrix layer.

17. A display according to claim 16, further comprising:

a thin film transistor formed between said projecting insulating layer and said substrate and having a pair of source/drain regions and a gate electrode, to which a gate line is connected,

wherein said light shielding layer formed of the same layer as that constituting said black matrix layer is formed to extend up to said gate line.

18. A display according to claim 12, wherein said projecting insulating layer has a finely uneven diffusion region at the upper surface thereof.

19. A display according to claim 12, wherein a side end of said projecting insulating layer has an inclined side surface; and

there is further provided a reflecting film formed not at the side surface of said projecting insulating layer but at the upper surface of said projecting insulating layer.

20. A display according to claim 12, wherein a side end of said projecting insulating layer has an inclined side surface; and

there is further provided a reflecting film formed at the upper surface and side surface of said insulating layer.

21. A display according to claim 12, further comprising:

a thin film transistor formed between said projecting insulating layer and said substrate and having a pair of source/drain regions and a gate electrode; and

a storage capacitance having a storage capacitance line,

wherein said light shielding layer is formed of a layer constituting said gate electrode and a layer constituting said storage capacitance line.

22. A display according to claim 21, wherein the layer constituting said gate electrode and the layer constituting said storage capacitance line are formed of the same layer.

23. A display according to claim 12, wherein said second distance in said reflective region is substantially half of said first distance in said transmissive region.